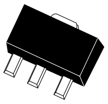
Central™
Semiconductor Corp.

CBCX68
CBCX69

SILICON COMPLEMENTARY SMALL SIGNAL TRANSISTORS



SOT-89 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBCX68, CBCX69 types are complementary silicon transistor manufactured by epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring high current capability.

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Collector-Emitter Voltage	V_{CES}	25	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	1.0	A
Collector Current-Peak	I_{CM}	2.0	A
Base Current	I_B	100	mA
Base Current Peak	I_{BM}	200	mA
Power Dissipation	P_D	1.2	W
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Temperature	Θ_{JA}	104	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{CBO}	V_{CB}=25V			100	nA
I_{CBO}	V_{CB}=25V, T_A=150°C				μA
I_{EBO}	V_{EB}=5.0V			10	μA
BV_{CBO}	I_C=10μA	25			V
BV_{CEO}	I_C=10mA	20			V
BV_{EBO}	I_E=1.0μA	5.0			V
$V_{CE(SAT)}$	I_C=1.0A, I_B=100mA			0.5	V
$V_{BE(ON)}$	V_{CE}=10V,I_C=5.0mA		0.6		V
$V_{BE(ON)}$	V_{CE}=1.0V, I_C=1.0A			1.0	V
h_{FE}	V_{CE}=10V,I_C=500mA	50			
h_{FE}	V_{CE}=1.0,I_C=500mA	85		375	
h_{FE}	V_{CE}=1.0V, I_C=1.0A	60			
f_T	V_{CE}=5.0V,I_C=10mA, f=20MHz	65			MHz

R4 (19-December 2001)

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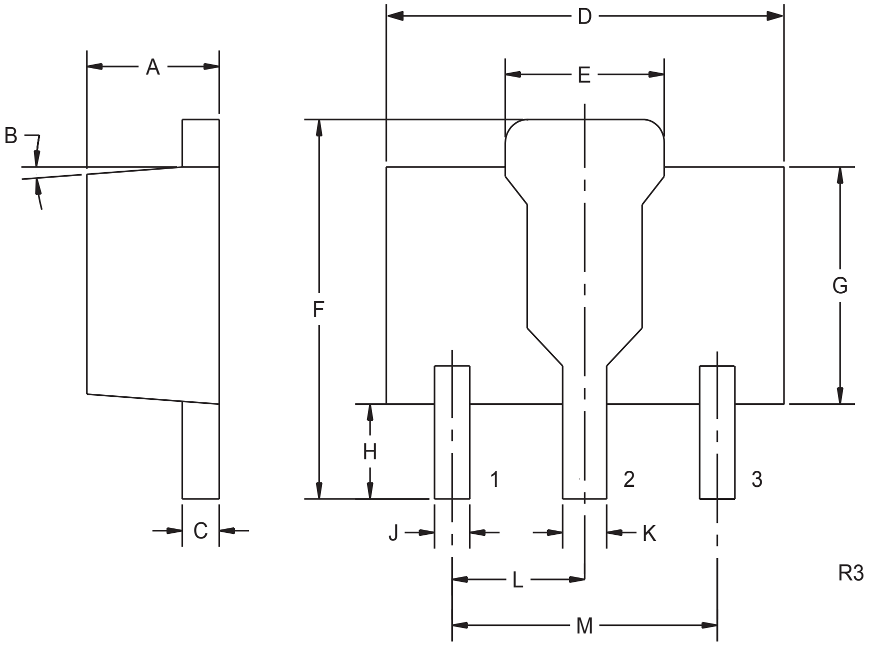
MECHANICAL OUTLINE - SOT-89



BOTTOM VIEW

LEAD CODE:

1) EMITTER
2) COLLECTOR
3) BASE

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.055	0.067	1.40	1.70
B	4°		4°	
C	0.016	0.018	0.40	0.46
D	0.173	0.185	4.40	4.70
E	0.070	0.074	1.79	1.87
F	0.146	0.177	3.70	4.50
G	0.094	0.106	2.40	2.70
H	0.028	0.051	0.70	1.30
J	0.015	0.019	0.38	0.48
K	0.019	0.023	0.48	0.58
L	0.059		1.50	
M	0.118		3.00	

SOT-89 (REV: R3)